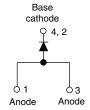


Vishay Semiconductors

Schottky Rectifier, 3.5 A





D-PAK (TO-252AA)

PRODUCT SUMMARY					
Package	D-PAK (TO-252AA)				
I _{F(AV)}	3.5 A				
V_{R}	30 V				
V _F at I _F	See Electrical table				
I _{RM}	50 mA at 125 °C				
T _J max.	150 °C				
Diode variation	Single die				
E _{AS}	8 mJ				

FEATURES

- Popular D-PAK outline
- Small foot print, surface mountable



- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- \bullet Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^{\circ}\text{C}$

DESCRIPTION

The VS-30WQ03FNPbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and small foot prints on PC board. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Rectangular waveform	3.5	Α			
V _{RRM}		30	V			
I _{FSM}	t _p = 5 µs sine	535	Α			
V _F	3 Apk, T _J = 125 °C	0.35	V			
T _J	Range	- 40 to 150	°C			

VOLTAGE RATINGS						
PARAMETER SYMBOL VS-30WQ03FNPbF UNITS						
Maximum DC reverse voltage	V_{R}	30	V			
Maximum working peak reverse voltage	V_{RWM}	30	V			

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST COND	TEST CONDITIONS			
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 134 °C	, rectangular waveform	3.5		
Maximum peak one cycle non-repetitive surge current		5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated	535	Α	
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	90		
Non-repetitive avalanche energy	E _{AS}	$T_J = 25$ °C, $I_{AS} = 2$ A, $L = 4$ mH		8	mJ	
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero Frequency limited by T _J maximo	1.0	Α		

VS-30WQ03FNPbF

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ELECTRICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS			
		3 A	T _{.1} = 25 °C	0.45	V		
Maximum forward voltage drop	V _{EM} (1)	6 A	11 = 23 0	0.52			
See fig. 1	VFM (*)	3 A	T _J = 125 °C	0.35			
		6 A	1J = 125 C	0.46			
Maximum reverse leakage current	I _{RM} ⁽¹⁾	T _J = 25 °C	V _R = Rated V _R	2	- mA		
See fig. 2		T _J = 125 °C	VR = nateu VR	50			
Threshold voltage	V _{F(TO)}	T - T movimum		0.22	٧		
Forward slope resistance	r _t	$T_J = T_J$ maximum		32.86	mΩ		
Typical junction capacitance	C _T	V _R = 5 V _{DC} (test signal range	290	pF			
Typical series inductance	L _S	Measured lead to lead 5 mm	5.0	nH			
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs			

Note

 $^{^{(1)}\,}$ Pulse width $<300~\mu s,$ duty cycle <2~%

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T _J ⁽¹⁾ , T _{Stg}		- 40 to 150	°C		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation See fig. 4	4.7	°C/W		
Approximate weight			0.3	g		
Approximate weight			0.01	OZ.		
Marking device		Case style D-PAK (similar to TO-252AA)	30WQ	03FN		

Note

 $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink



Schottky Rectifier, 3.5 A

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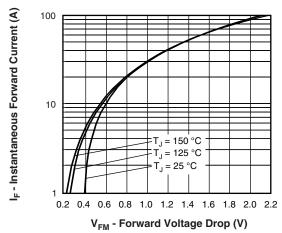


Fig. 1 - Maximum Forward Voltage Drop Characteristics

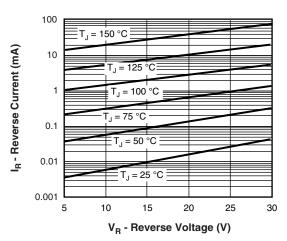


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

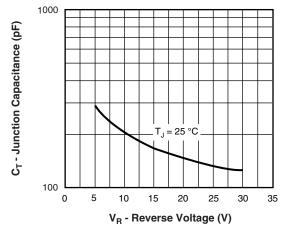


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

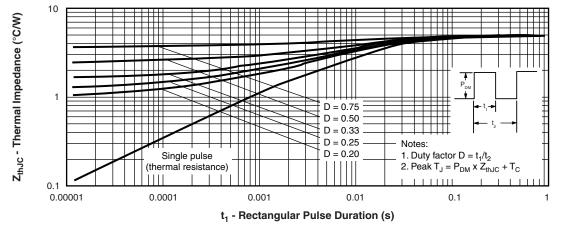
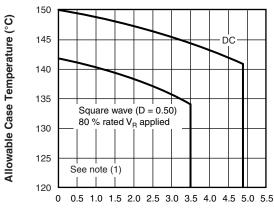


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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Schottky Rectifier, 3.5 A





I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

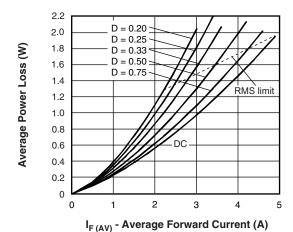


Fig. 6 - Forward Power Loss Characteristics

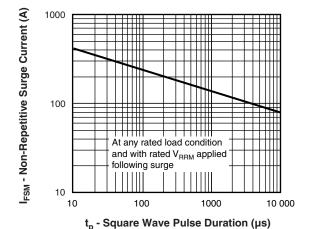


Fig. 7 - Maximum Non-Repetitive Surge Current

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80 \%$ rated V_R

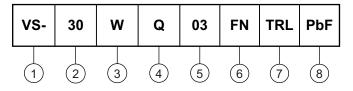


Schottky Rectifier, 3.5 A

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (3.5 A)

Package identifier:

W = D-PAK

4 - Schottky "Q" series

5 - Voltage rating (03 = 30 V)

6 - FN = TO-252AA (D-PAK)

7 • None = Tube (50 pieces)

• TR = Tape and reel

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

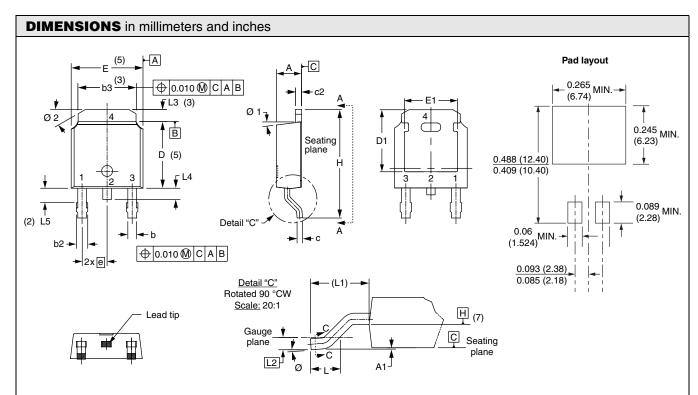
PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95016</u>				
Part marking information	www.vishay.com/doc?95059			
Packaging information	www.vishay.com/doc?95033			



Vishay High Power Products

D-PAK (TO-252AA)



SYMBOL	MILLIM	MILLIMETERS		INCHES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	2.18	2.39	0.086	0.094		
A1	-	0.13	-	0.005		
b	0.64	0.89	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215	3	
С	0.46	0.61	0.018	0.024		
c2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245	5	
D1	5.21	-	0.205	-	3	
Е	6.35	6.73	0.250	0.265	5	
E1	4.32	-	0.170	-	3	

SYMBOL	MILLIMETERS		INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	BSC	0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51	0.51 BSC		BSC	
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- $^{(7)}$ Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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